Micro Calorimeters -Production Technologies and Technological Challenges

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Y2

*L*<sub>β1</sub>

Υı

 $L_{\alpha 1}$ 

0

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50 keV

 $\gamma_3$ 

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Micro Calorimeters -Production Technologies and Technological Challenges

- reminder: metallic magnetic calorimeters
- fab technologies and fab challenges

Y2

 $L_{\beta 1}$ 

 $L_{\alpha 1}$ 

0

examples: absorber fab, through-silicon vias, <sup>35</sup>
Josephson junctions, ...

50 keV

# metallic magnetic calorimeter (MMC)



fundamental limit on energy resolution:  $\Delta E_{\rm FWHM} \simeq 2.36 \sqrt{4k_{\rm B}C_{\rm Abs}T^2} \sqrt{2} \left(\frac{\tau_0}{\tau_1}\right)^{1/4}$ 

## key features of metallic magnetic calorimeters



outstanding interplay between highly sensitive magnetic thermometer and near quantum-limited amplifier  $\gamma$ -spectroscopy of a mixed Pu sample using MMCs



Pu isotope ratios same as determined with mass spectrometry

C. Bates et al., J. Low Temp. Phys. 184 (2016) 351

# MMC all around the world







# state-of-the-art detector geometries



# fabrication of metallic magnetic calorimeters



mask writer

mask aligner

UHV sputtering

wet bench chemistry d

dry etching maskless aligner

- standard UV photolithography
- process with 10 (18) layers

# why dealing with microfabrication?

semiconductor industries operate well-established fabrication facilities (foundries)



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but: MMC + SQUID fabrication requires special fabrication capabilities

# fabrication of metallic magnetic calorimeters



mask writer

mask aligner

UHV sputtering

wet bench chemistry

dry etching maskless aligner

- standard UV photolithography
- Nb based process with 10 (18) layers
- structure sizes:  $2 \mu m 5 cm$
- layer thicknesses: 2 nm 200 μm
- non-conventional processes, materials











# ,non-standard' microfabrication portfolio for fabricating MMCs



# ,non-standard' microfabrication portfolio for fabricating MMCs



# example: process description for 'standard' soft X-ray detectors

## detectors with meander-shaped pickup coils and not including thru-substrate vias

layer no.	layer name	material	thickness (nm)	process	purpose
1	Nb1	Nb	250	sputtering + RIE	pickup coil, wiring
2	lso1a	Nb <sub>2</sub> O <sub>5</sub> SiO <sub>2</sub>	50 175	anodization lift-off + sputtering	insulation
3	lso1b	SiO <sub>2</sub>	175	lift-off + sputtering	insulation
4	AuPd	Nb / AuPd / Nb	2 / 160 / 2	lift-off + sputtering	resistors
5	Nb2	Nb	500	lift-off + sputtering	wiring
6	Therm	Nb / Au	2 / 200	lift-off + sputtering	detector thermalization
7	Sens	Nb / Au:Er / Au	2 / 1300 / 200	lift-off + sputtering	temperature sensor
8	Seed	Nb / Au / Nb	2 / 200 / 50	sputtering + ion milling + RIE	seed layer for electroplating
9	Abs	Au	5000	electroplating	particle absorber

# overhanging (free-standing) absorbers



## reduction of athermal phonon loss



## more efficient use of space on chip



# fabrication of overhanging (free-standing) absorbers

process based on two subsequent resist layers (positive/negative) that are stacked onto each other



challenges (selection):

- resist aspect ratio: 1:100
- structured resist immersed into chemicals
- resist intercompatibility
- absorber area / support structure area

AZ nLOF2070	): <i>h</i> < 7 μm
AZ 15nXT:	<i>h</i> < 15 μm
AZ 125nXT:	<i>h</i> > 15 μm
AZ 6632:	<i>h</i> < 5 μm

# vertical interconnect accesses (vias) through the substrate

# deep reactive ion etching (DRIE) to make holes through the substrate



## allow particles to fly through the substrate



#### thermal isolation of sensitive detector parts



## creation of metallic vias through the substrate



## wafer backside processing with AI hard mask technique and DRIE



big challenge: wafer frontside contains almost finished detector

in-situ deposited Nb/Al-AlOx/Nb trilayer with selective niobium etching (SNEP)



## challenge: control of an angstrom thick oxide layer

# fabrication of Josephson junctions

## in-situ deposited Nb/Al-AlOx/Nb trilayer with selective niobium etching (SNEP)



presently: smallest junction size (~3 μm) set by size of insulation window (~2 μm) challenge: reaching sub-μm lateral size

# microfabrication challenges: a selection

- large contiguous arrays ( $A_{det} > 100 \text{ cm}^2$ ,  $N_{det} > 10^4$ )
- no. of detector for large-scale experiments
- detector yield
- operation at mK temperatures
  - intrinsic film stress, thermal contraction
- new sensor / absorber materials
  - → Ag:Er, Au/Bi, ...
- control of surface morphology, film growth
- detector complexity
- no. of wiring layers

planarization (CMP, Nb embedding, ...)





## summary





# thank you for your attention!

